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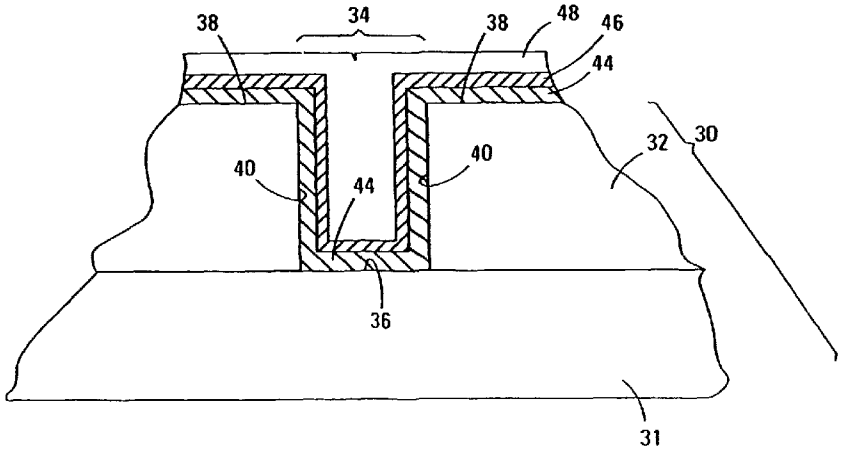
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(54) Title: METHOD FOR FORMING CONDUCTIVE MATERIAL IN OPENING AND STRUCTURE REGARDING SAME



(57) Abstract: Method and structure use support layers to assist in planarization processes to form conductive materials (*e.g.*, a Group VIII metal) in an opening. Further, such method and structure may use a Group VIII metal as an etch stop or end point for the planarization process with subsequent etching to remove undesired portions of the Group VIII metal. One exemplary method of providing a conductive material (44) in an opening includes providing a substrate assembly having at least one surface and providing an opening defined through the surface of the substrate assembly. The opening is defined by at least one surface. At least one conductive material (44) (*e.g.*, at least one Group VIII metal such platinum and/or rhodium) is formed within the opening on the at least one surface defining the opening and on at least a portion of the substrate assembly surface. A support film (46) (*e.g.*, an oxide material) is formed over the conductive material and a fill material (48) (*e.g.*, a resist material) is formed over at least a portion of the support film. The fill material at least fills the opening. Thereafter, at least the fill material outside of the opening is removed by planarization. The support film outside of the opening, the at least one conductive material outside of the opening, the fill material within the opening, and the support film within the opening are then removed.

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